

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes a semiconductor substrate having one principal plane on which a plurality of electrodes are formed. A film which is made of polymer with a low dielectric constant is formed over the gate and drain electrodes so as to insulate the gate and drain electrodes from the source electrode. A chip surface electrode is formed over the low-dielectric-constant polymer film and the source electrode, and connected to a ground potential. The source electrode is provided with a ground potential through the chip surface electrode.